

isc Silicon NPN Power Transistor

2N6322

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-: V_{(BR)CEO}= 200V(Min)
- High Current Capability
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

• Designed for power amplifier and high-speed switching applications.

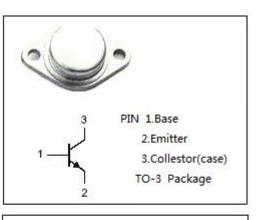
PARAMETER	VALUE	UNIT					
Collector-Base Voltage	300	V					
Collector-Emitter Voltage	200	V					
Emitter-Base voltage	5	V					
Collector Current-Continuous	30	А					
Base Current-Continuous	10	А					
Pc Collector Power Dissipation @ Tc=25°C		W					
Junction Temperature	200	°C					
Storage Temperature Range	-65~200	°C					
	PARAMETER Collector-Base Voltage Collector-Emitter Voltage Emitter-Base voltage Collector Current-Continuous Base Current-Continuous Collector Power Dissipation @ Tc=25°C Junction Temperature	PARAMETERVALUECollector-Base Voltage300Collector-Emitter Voltage200Emitter-Base voltage5Collector Current-Continuous30Base Current-Continuous10Collector Power Dissipation @ T_c=25°C200Junction Temperature200					

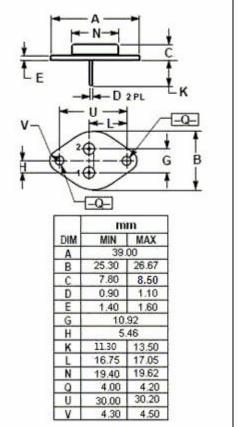
ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT	
R _{th j-c}	Thermal Resistance, Junction to Case	0.5	°C/W	

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isc website: www.iscsemi.com



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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 30mA ; I _B = 0	200			V
V _{CE(sat)} -1	Collector-Emitter Saturation Voltage	I _C = 20A; I _B = 2A			1.5	V
V _{CE(sat)} -2	Collector-Emitter Saturation Voltage	I _C = 30A; I _B = 6A			3.0	v
$V_{\text{BE}(\text{on})}$	Base-Emitter On Voltage	I _C = 30A ; V _{CE} = 5V			2.5	V
І _{сво}	Collector Cutoff Current	V _{CB} = 300V ; I _E = 0			2.0	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = 200V ; I _B = 0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			0.5	mA
h _{FE-1}	DC Current Gain	I _C = 5A ; V _{CE} = 5V	40		150	
h _{FE-2}	DC Current Gain	Ic= 20A ; Vce= 5V	12			
h _{FE-3}	DC Current Gain	I _C = 30A ; V _{CE} = 5V	6			
f⊤	Current-Gain—Bandwidth Product	I _C =1A ; V _{CE} = 10V	10			MHz

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